

In The Claims

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1. (currently amended) A substrate cutting method characterized by irradiating a substrate with an ultrashort pulse laser to cut it, wherein a pulse width of said ultrashort pulse laser is equal to or less than 1 picosecond, and said ultrashort pulse laser emits a plurality of pulses having an interpulse separation of 3 to 30 picoseconds.

2. (canceled).

3. (previously amended) A substrate cutting method as set forth in Claim 1, characterized in that a surface layer of the substrate is irradiated with said laser.

Claims 4-6. (cancelled)

Claim 7. (original) A substrate cutting method as set forth in Claim 1, characterized in that said substrate is a semiconductor wafer formed with a number of elements and said ultrashort pulse laser is irradiated along the scribed lines between said elements.

Claim 8. (canceled)

9. (original) A substrate cutting method as set forth in Claim 3, characterized in that said substrate is a semiconductor wafer formed with a number of elements and said ultrashort pulse laser is irradiated along the scribed lines between said elements.

10. (currently amended) A substrate cutting method as set forth in ~~Claim 4 or 5~~ 1 or Claim 2, characterized in that said substrate is a semiconductor wafer formed with a number of elements and said ultrashort pulse laser is irradiated along the scribed lines between said elements.

11. (previously amended) A substrate cutting method as set forth in Claim 10, characterized in that the thickness of said semiconductor wafer is equal to or less than 50 μm .

12. (original) A substrate cutting method as set forth in Claim 10, characterized in that said semiconductor wafer has a batch-processed adhesive agent layer on the back.

13. (original) A substrate cutting method as set forth in Claim 11, characterized in that said semiconductor wafer has a batch-processed adhesive agent layer on the back.

14. (original) A substrate cutting method as set forth in Claim 10, characterized in that the back of said semiconductor wafer is drawn by an x-y table.

15. (original) A substrate cutting method as set forth in Claim 11, characterized in that the back of said semiconductor wafer is drawn by an x-y table.

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16. (original) A substrate cutting method as set forth in Claim 13, characterized in that the back of said semiconductor wafer is drawn by an x-y table.

17. (original) A substrate cutting method as set forth in Claim 10, characterized in that said laser is irradiated to the semiconductor wafer excluding the peripheral portion thereof.

18. (original) A substrate cutting method as set forth in Claim 11, characterized in that said laser is irradiated to the semiconductor wafer excluding the peripheral portion thereof.

19. (original) A substrate cutting method as set forth in Claim 13, characterized in that said laser is irradiated to the semiconductor wafer excluding the peripheral portion thereof.

20. (original) A substrate cutting method as set forth in Claim 16, characterized in that said laser is irradiated to the semiconductor wafer excluding the peripheral portion thereof.
